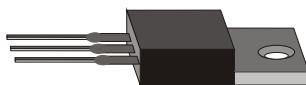


MBR20100LCT

Schottky Barrier Diodes Low Forward Voltage
20 A Total (10A Per Diode Leg)

I_O



FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- Dual rectifier construction
- High temperature soldering guaranteed:260° C/10 seconds.,, 0.25"(6.35mm)from case
- Component in accordance to RoHS 2011/65/ EU

MECHANICAL DATA

- Case: JEDEC ITO-220AB molded plastic body
- Terminals: Lead solderable per MIL-STD-750,method 2026
- Polarity: As marked
- Mounting Position: Any
- Weight: 1.81 gram
- * Lead Free Finish/RoHS Compliant

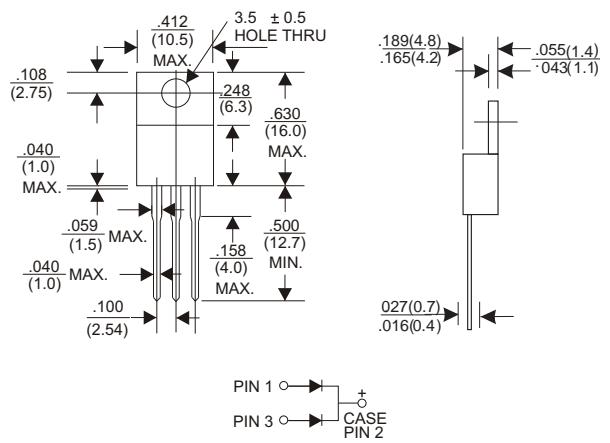
VOLTAGE RANGE

100 Volts

CURRENT

20.0Ampere

TO-220AB



Dimensions in inches and (millimeters)

RATINGS (Per Diode Leg)

Rating	Symbol	MBR20100LCT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	100	V
Average Rectified Forward Current (Rated V _R) T _C = 133°C	I _{F(AV)}	10	A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz) T _C = 133°C	I _{FRM}	20	A
Typical Instantaneous Forward Voltage (I _F = 10Amps, T _C = 25°C)	V _F	0.72	V
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I _{FSM}	200	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	5	A
Operating Junction Temperature	T _J	- 65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs
Maximum Instantaneous Reverse Current (Rated dc Voltage, T _C = 125°C) (Rated dc Voltage, T _C = 25°C)	I _R	6.0 0.05	mA

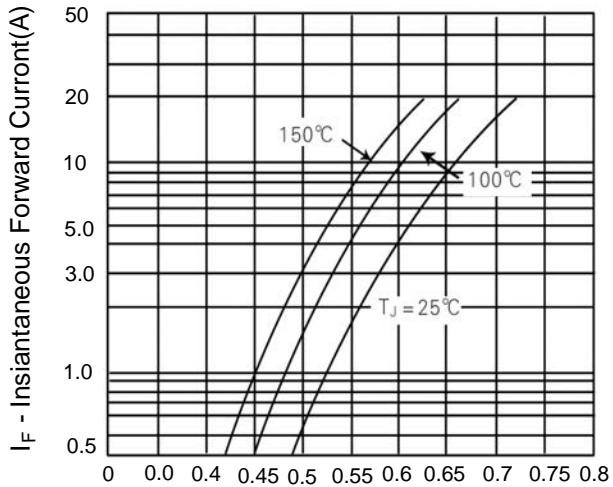


Figure 1. Typical Forward Voltage Per Diode

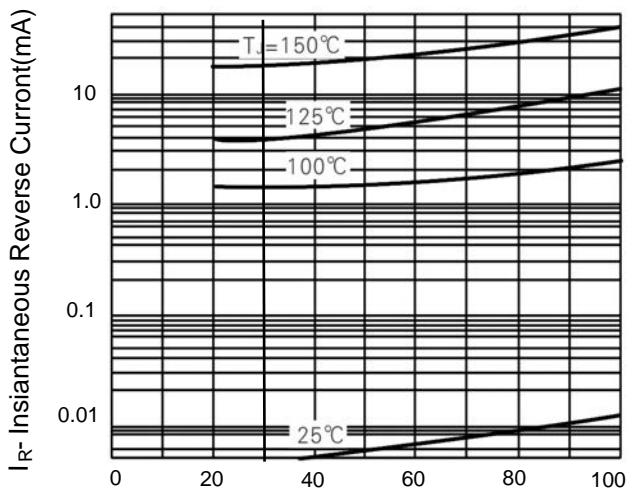


Figure 2. Typical Reverse Current Per Diode

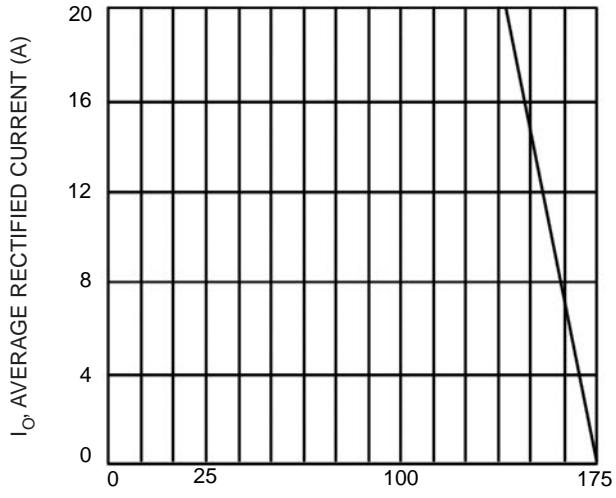


Fig.3 Forward Current Derating Curve

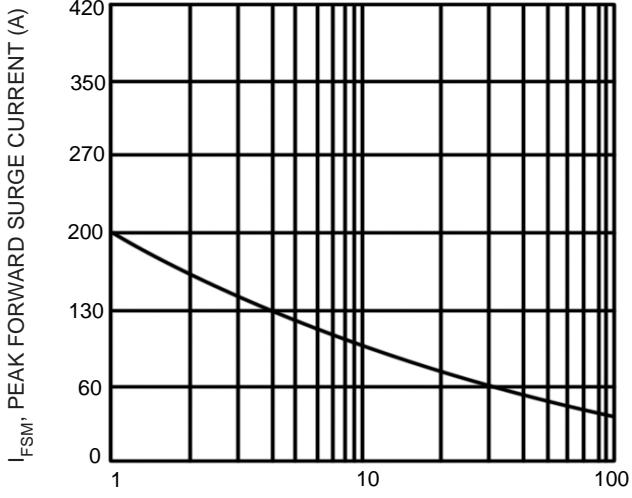


Fig.4 Max Non-Repetitive Surge Current